

Part Number: A001T67 Product State: Alpha Build

Rev. 0.4 - Nov. 2023

100 KHz – 67 GHz Amplifier

Description

A001T67 is an ultrawide band amplifier that operates from 100 KHz to 67 GHz. The amplifier is packaged in a hermetic package with easy to use 1.85 mm coaxial connectors. The device features good RF matching across the entire operating band for both input and output. This device only requires positive bias voltage.

Features

- Coaxial package
- 14 dB Gain
- 4.6 dB Noise Figure
- 12 dB return loss
- 20 dBm P3dB
- Positive bias voltage
- 20 dB Reverse isolation
- 1.85 mm connectors



Applications

- Communication systems
- Datacenters
- Test and Measurement



Rendered production device



IMPORTANT NOTICE: more Information on warranty, changes, rights, notices, and other information are presented at the end of this data sheet. If the sheet is not present, refer to <u>www.nuphotonics.com</u> for the company issued data sheet.

Electrical Specifications	; (T _{op} 23 ± 3°c, unless	otherwise specified)
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Parameter	Min.	Тур.	Max.	Unit	Test Conditions
Gain		16		dB	100 KHz – 10 GHz
		15			10 – 50 GHz
		14			50 – 60 GHz
		10			60 – 67 GHz
Noise Figure		6			1 - 10 GHz
		4.3		dB	10 – 20 GHz
		4.7			20 – 27 GHz
	10	17			100 KHz -20 GHz
Inputout Return loss	10	16.2		dB	20 – 40 GHz
	10	14.8			40 – 67 GHz
	10	15			100 KHz -20 GHz
Output Return loss	10	13		dB	20 – 40 GHz
	10	11.7			40 – 67 GHz
		17.5			100 KHz – 10 GHz
P1dB		17		dBm	10 – 20 GHz
		17.5			20 – 27 GHz
P3dB		21			100 KHz – 10 GHz
		21		dBm	10 – 20 GHz
		19			20 – 27 GHz
OIP3		25			100 KHz – 10 GHz
		25		dBm	10 – 20 GHz
		25.5			20 – 27 GHz



Absolute Maximum Ratings

Parameter	Symbol	Condition	Min.	Max.	Unit
Drain Voltage	V			8	V
Drain Current ¹	l _d			150	mA
Storage Temperature	T_{stg}		-65	120	°C
Storage Humidity	H_{stg}			85	% r.H.
Operating Temperature	T _{op}		-40	85	°C
ESD Susceptibility ²		HBM		1000	V
Input Power	P _{in}	CW		25	dBm

Operating at maximum ratings for a prolonged period will cause damage to the device.

¹ Drain current is limited by the junction temperature.

² ESD sensitive device, proper ESD protection procedures must be followed.

Pin Configuration



Pin Number	Function
1	Gate Voltage 1 (V _{G1})
2	Gate Voltage 2 (V _{G2})
3	Detector Voltage (VDET)
4	Drain Voltage (V _{DD})

Power On Procedure

- 1) Set V_{G1} to 0v
- 2) Set V_{DD} to 6v
- Adjust V_{G1} more positive until desired drain current is achieved (Typically 0.65V for Id = 135 mA)
- 4) Apply RF input signal

Power OFF Procedure

- 1) Remove RF input signal
- 2) Set V_{G1} to 0V
- 3) Slowly decrease V_{DD} to 0V



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Typical performnace curves (T_{op} 23 ± 3°c, Id = 125 mA)



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Data taken 1 – 27 GHz at 1 GHz steps. Data was interpolated to fill in data points.



Device Dimensions (all units in mm)





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Definitions: Product State

Alpha Build: Devices in Alpha build are in internal engineering build and testing stages. Major changes may happen for production build.

Beta Build: Devices in Beta build are for external customer and engineering sample testing stages. Minor changes may happen for production build.

Production Build: Customer ready devices. Small appearance changes may occur between devices.

Obsolete: Currently not supported.

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